

Silicon NPN Power Transistors

2SD1885

DESCRIPTION

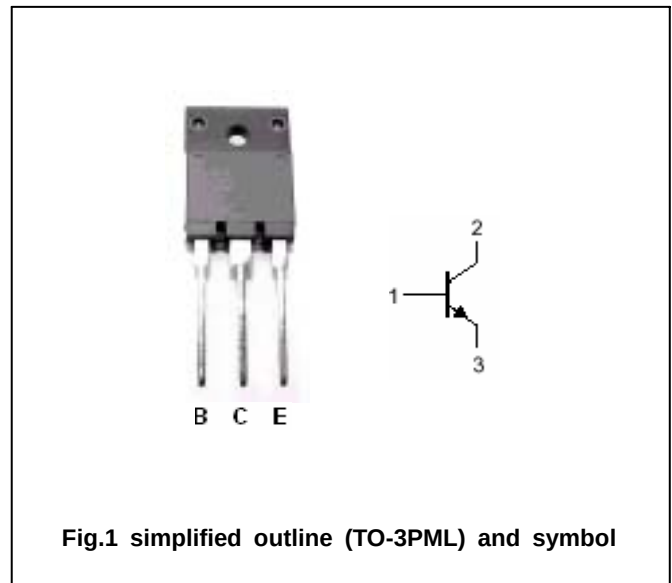
- With TO-3PML package
- High breakdown voltage
- High reliability
- High speed

APPLICATIONS

- Color TV horizontal deflection output.
- Color display horizontal deflection output.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_{CM}	Collector current-peak		20	A
P_C	Collector power dissipation		3.0	W
		$T_C=25^\circ\text{C}$	60	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A; I_B=1 A$			5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A; I_B=1 A$			1.5	V
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA; I_B=0$	800			V
I_{EBO}	Emitter cut-off current	$V_{EB}=4V; I_C=0$			1	mA
I_{CBO}	Collector cut-off current	$V_{CB}=800V; I_E=0$			10	μA
I_{CES}	Collector cut-off current	$V_{CE}=1500V; R_{BE}=0$			1	mA
h_{FE-1}	DC current gain	$I_C=1 A ; V_{CE}=5V$	8			
h_{FE-2}	DC current gain	$I_C=5A ; V_{CE}=5V$	5		10	
t_f	Fall time	$I_C=4A; R_L=50 \Omega ; I_{B1}=0.8A$ $I_{B2}=-1.6A V_{CC}=200V$		0.1	0.3	μs

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PACKAGE OUTLINE

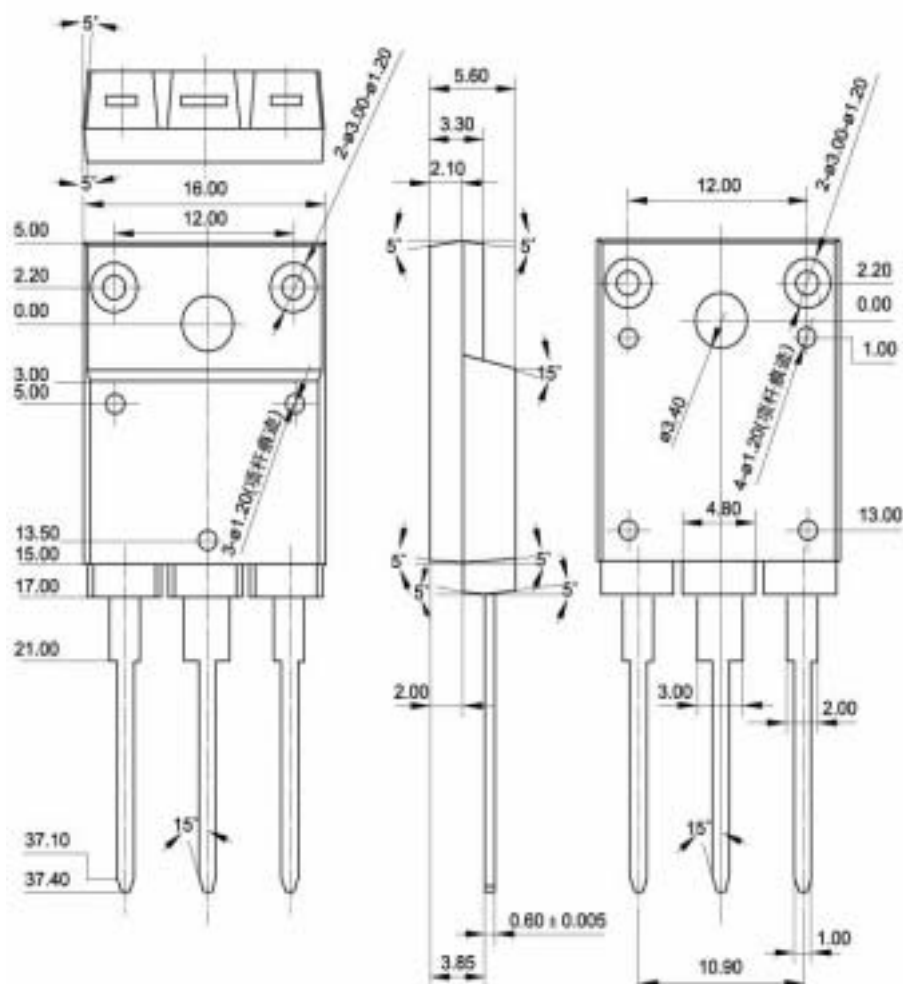


Fig.2 Outline dimensions

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